



#### **60V N-Channel Enhancement Mode MOSFET**

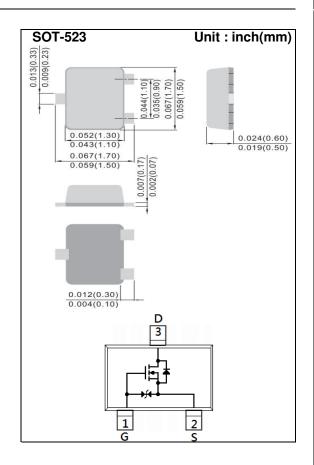
Voltage 60 V Current 160mA

#### **Features**

- RDS(ON), VGS@10V, ID@160mA<4.2Ω
- RDS(ON), VGS@4.5V, ID@100mA<5Ω
- RDS(ON) , VGS@2.5V, ID@50mA<7Ω</li>
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

### **Mechanical Data**

- Case: SOT-523 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00007 ounces, 0.002 grams
- Marking: E8L



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	160	mA
Pulsed Drain Current		I <sub>DM</sub>	800	mA
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	223	mW
	Derate above 25°C		1.8	mW/°C
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C
Typical Thermal resistance - Junction to Ambient (Note 3)		$R_{ hetaJA}$	560	°C/W





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.8	1.2	1.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_{D}=160mA$	-	2.5	4.2	Ω
		V <sub>GS</sub> =4.5V,I <sub>D</sub> =100mA	-	2.8	5	
		V <sub>GS</sub> =2.5V,I <sub>D</sub> =50mA	-	3.7	7	
		V <sub>GS</sub> =1.8V,I <sub>D</sub> =10mA	-	12	-	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}=60V, V_{GS}=0V$	-	0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	<u>+</u> 1.0	<u>+</u> 10	uA
Dynamic (Note 4)						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =15V, I <sub>D</sub> =160mA, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.7	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.33	-	
Gate-Drain Charge	$Q_{gd}$		-	0.2	-	
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	15	-	pF
Output Capacitance	Coss		-	8.4	-	
Reverse Transfer Capacitance	Crss		-	4.2	-	
Turn-On Delay Time	td <sub>(on)</sub>	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	7	-	ns
Turn-On Rise Time	tr	$\begin{array}{l} V_{DD}{=}10V,\ I_{D}{=}160mA,\\ V_{GS}{=}10V,\\ R_{G}{=}6\Omega \end{array}$	-	22	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	21	-	
Turn-Off Fall Time	tf		-	25	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source			-	-	160	mA
Diode Forward Current	I <sub>S</sub>					
Diode Forward Voltage	$V_{\text{SD}}$	I <sub>S</sub> =160mA, V <sub>GS</sub> =0V	-	0.8	1.1	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
- 4. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

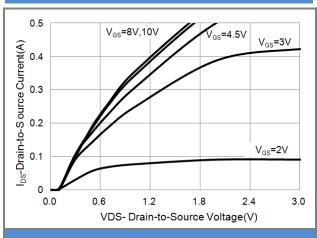


Fig.1 On-Region Characteristics

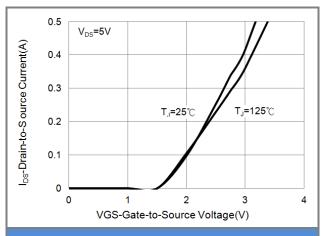


Fig.2 Transfer Characteristics

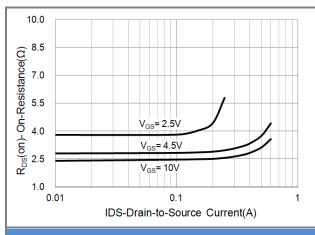


Fig.3 On-Resistance vs. Drain Current

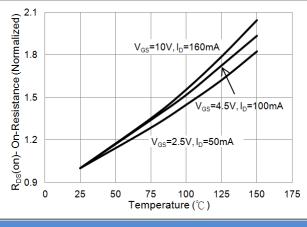
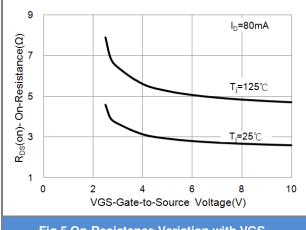
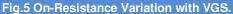


Fig.4 On-Resistance vs. Junction temperature





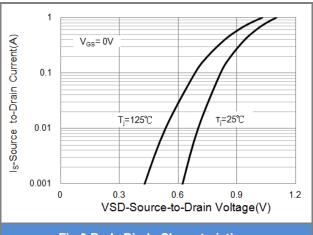


Fig.6 Body Diode Characteristics





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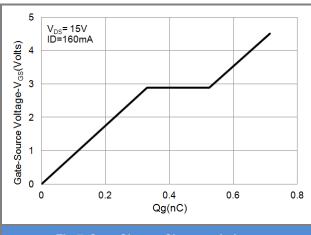
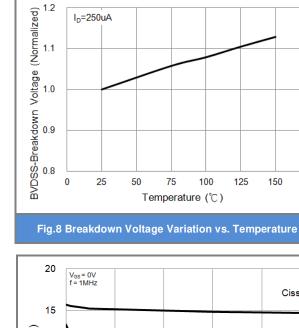


Fig.7 Gate-Charge Characteristics



I<sub>D</sub>=250uA

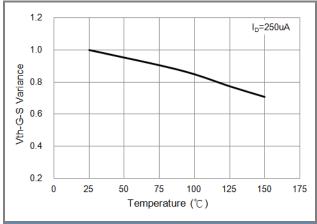
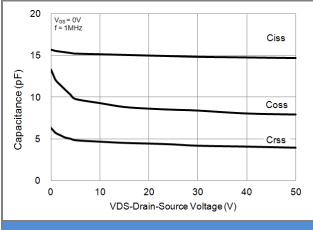


Fig.9 Threshold Voltage Variation with Temperature.



125

150

175

Fig.10 Capacitance vs. Drain-Source Voltage.

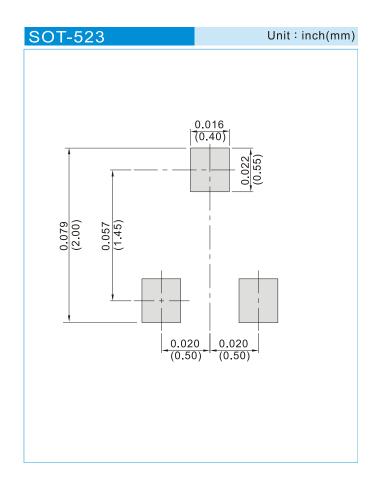




#### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version	
PJE138L_R1_00001	SOT-523	4K pcs / 7" reel	E8L	Halogen free	

### **MOUNTING PAD LAYOUT**







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